

Vishay Semiconductors

Silicon NPN Phototransistor, RoHS Compliant



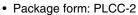
TEMT3700 is a high speed silicon NPN epitaxial planar

phototransistor in a miniature PLCC-2 package for surface

mounting on printed boards. The device is sensitive to visible

FEATURES

· Package type: surface mount





- · High photo sensitivity
- · High radiant sensitivity
- · Suitable for visible and near infrared radiation



- Angle of half sensitivity: $\phi = \pm 60^{\circ}$
- · Package notch indicates collector
- Package matched with IR emitter series VSML3710
- Floor life: 1 year, MSL 2, acc. J-STD-020
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

- · Photo interrupters
- · Miniature switches
- Counters
- Encoders
- · Position sensors
- · Ligth sensors

PRODUCT SUMMARY			
COMPONENT	I _{ca} (mA)	φ (deg)	λ _{0.1} (nm)
TEMT3700	0.5	± 60	450 to 1080

Note

DESCRIPTION

and near infrared radiation.

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TEMT3700-GS08	Tape and reel	MOQ: 7500 pcs, 1500 pcs/reel	PLCC-2	
TEMT3700-GS18	Tape and reel	MOQ: 8000 pcs, 8000 pcs/reel	PLCC-2	

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Collector emitter voltage		V_{CEO}	70	V	
Emitter collector voltage		V _{ECO}	5	V	
Collector current		Ic	50	mA	
Collector peak current	$t_p/T \le 0.1, t_p \le 10 \ \mu s$	I _{CM}	100	mA	
Power dissipation		P _V	100	mW	
Junction temperature		Tį	100	°C	
Operating temperature range		T _{amb}	- 40 to + 100	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	Acc. reflow solder profile fig. 10	T _{sd}	260	°C	
Thermal resistance junction/ambient	Soldered on PCB with pad dimensions: 4 mm x 4 mm	R _{thJA}	400	K/W	

Note

T_{amb} = 25 °C, unless otherwise specified

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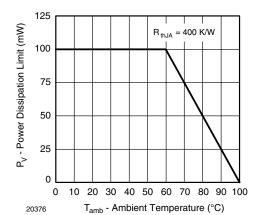


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	I _C = 1 mA	V _{(BR)CEO}	70			V
Collector emitter dark current	V _{CE} = 20 V, E = 0	I _{CEO}		1	200	nA
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz, E = 0	C _{CEO}		3		pF
Collector ligth current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm},$ $V_{CE} = 5 \text{ V}$	I _{ca}	0.25	0.5		mA
Angle of half sensitivity		φ		± 60		deg
Wavelength of peak sensitivity		λ_{p}		850		nm
Decree of an extent board of the		λ _{0.1}		450 to 1080		nm
Range of spectral bandwidth		λ _{0.5}		620 to 980		nm
Collector emitter saturation voltage	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm},$ $I_{C} = 0.1 \text{ mA}$	V _{CEsat}		0.15	0.3	٧
Disations fall times	$V_S = 5$ V, $I_C = 1$ mA, $\lambda = 950$ nm, $R_L = 1$ k Ω	t _r /t _f		6		μs
Rise time, fall time	V_S = 5 V, I_C = 1 mA, λ = 950 nm, R_L = 100 Ω	t _r /t _f		2		μs
Cut-off frequency	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega$	f _c		180		kHz

Note

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BASIC CHARACTERISTICS

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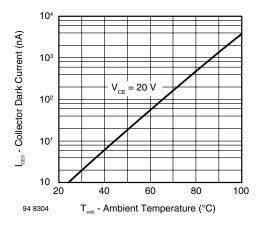


Fig. 2 - Collector Dark Current vs. Ambient Temperature

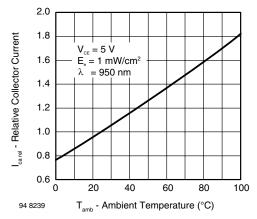


Fig. 3 - Relative Collector Current vs. Ambient Temperature



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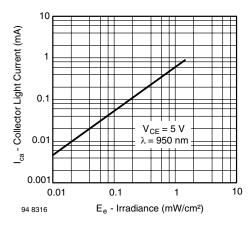


Fig. 4 - Collector Light Current vs. Irradiance

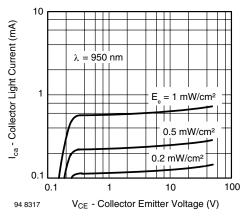


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

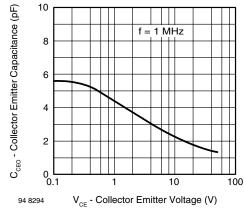


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

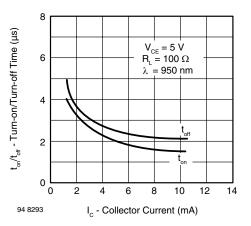


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

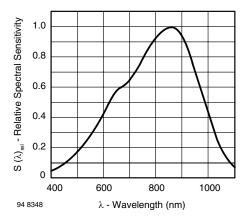


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

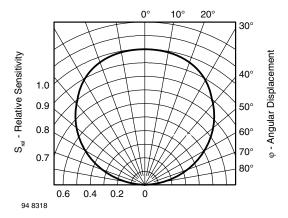
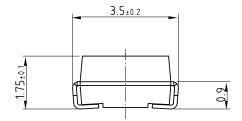


Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement

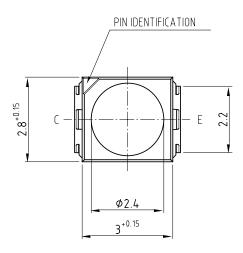
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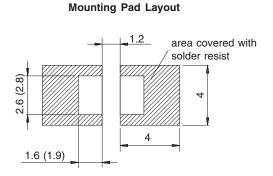


PACKAGE DIMENSIONS in millimeters









Drawing-No.: 6.541-5025.03-4 Issue: 5; 21.11.05

20350

SOLDER PROFILE

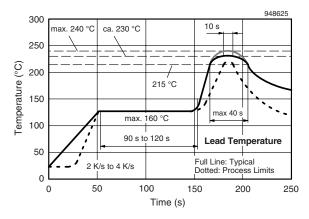


Fig. 10 - Lead Tin (SnPb) Reflow Solder Profile

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 1 year

Conditions: T_{amb} < 30 °C, RH < 60 %

Moisture sensitivity level 2, acc. to J-STD-020.

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 $^{\circ}$ C (+ 5 $^{\circ}$ C), RH < 5 $^{\circ}$ M.



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TAPE AND REEL

PLCC-2 components are packed in antistatic blister tape (DIN IEC (CO) 564) for automatic component insertion. Cavities of blister tape are covered with adhesive tape.

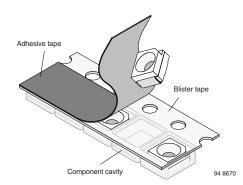


Fig. 11 - Blister Tape

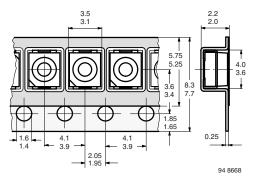


Fig. 12 - Tape Dimensions in mm for PLCC-2

MISSING DEVICES

A maximum of 0.5 % of the total number of components per reel may be missing, exclusively missing components at the beginning and at the end of the reel. A maximum of three consecutive components may be missing, provided this gap is followed by six consecutive components.

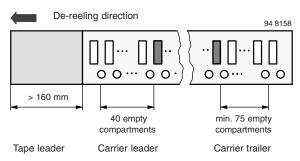


Fig. 13 - Beginning and End of Reel

The tape leader is at least 160 mm and is followed by a carrier tape leader with at least 40 empty compartments. The tape leader may include the carrier tape as long as the cover tape is not connected to the carrier tape. The least component is followed by a carrier tape trailer with a least 75 empty compartments and sealed with cover tape.

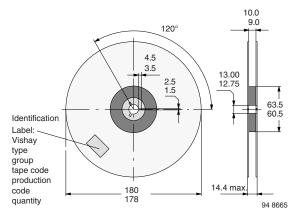


Fig. 14 - Dimensions of Reel-GS08

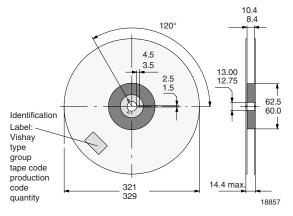


Fig. 15 - Dimensions of Reel-GS18

COVER TAPE REMOVAL FORCE

The removal force lies between 0.1 N and 1.0 N at a removal speed of 5 mm/s. In order to prevent components from popping out of the blisters, the cover tape must be pulled off at an angle of 180° with regard to the feed direction.



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